

L Number	Hits	Search Text	DB	Time stamp
1	519	SiGe same (HBT or (heterojunction near bipolar near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/20 13:27
2	184	(base near region) same (boron near concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/20 13:28
3	11	peak near Ge near concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/20 13:29
4	2	diffusion-limit\$3 near impurit\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/20 13:29
6	3	(SiGe same (HBT or (heterojunction near bipolar near transistor))) and ((base near region) same (boron near concentration)) and (peak near Ge near concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/20 13:30
5	2	(SiGe same (HBT or (heterojunction near bipolar near transistor))) and ((base near region) same (boron near concentration)) and (peak near Ge near concentration) and (diffusion-limit\$3 near impurit\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/20 13:33